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IN4500

SWITCHING DIODE:

FEATURES

- SILICON HIGH FORWARD CONDUCTANCE SWITCHING DIODE
- VOIDLESS* HERMETICALLY SEALED GLASS PACKAGE
- METALLURGICALLY BONDED (-1 TYPE)
 TX, TXV TYPES AVAILABLE PER MIL-S-19500/403
- EXCLUDES DO-35 DUMET CONSTRUCTION OPTION.

MAXIMUM RATINGS

Operating Temperature: -65°C to +175°C
 Storage Temperature: -65°C to +200°C
 Surge Current: 4 Amps ($t_p = 1\mu s$)
 Leakage Current: 100nA @ 75V, 25°C.

ELECTRICAL CHARACTERISTICS

at 25°C unless otherwise specified.

$V_{(BR)}$	V_{RWM} (working)	I_o (note 1)	I_f (surge) (1 sec)	I_f (surge) (1 μ sec)	T_{OP}	T_{STG}
Vdc	V(pk)	mAdc	A	A	°C	°C
80	75	300	0.5	4.0	-65 to +175	-65 to +200

CAPACITANCE $V_R = 0$ Volts $V_{sig} = 50$ mVpp $100KHz \leq f \leq 1$ MHz	V_{f1} @ $I_f = 250\mu$ Adc	V_{f2} @ $I_f = 1.0$ mA	V_{f3} @ $I_f = 10$ mA	V_{f4} @ $I_f = 20$ mA	V_{f5} @ $I_f = 300$ mA (pulse)	t_{rr} @ $I_f = I_R$ 10mAdc $R_L = 100$ ohms
pF	Vdc	Vdc	Vdc	Vdc	Vdc	ns
4 max.	.47 - .56	.52 - .60	.64 - .72	.67 - .77	1.1 max.	6.0 max.

OTE 1: DERATE 2.0 mAdc/°C For T_A Above 25°C.

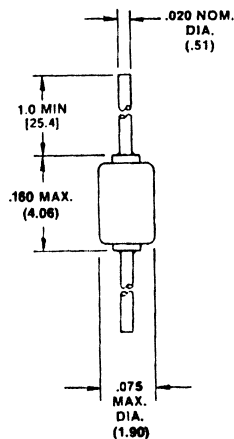
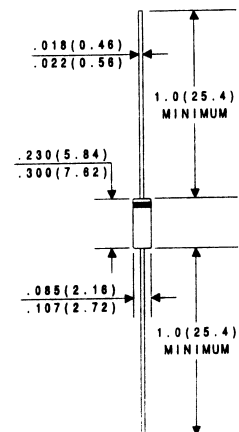


FIGURE 1
 PACKAGE DO-35

DO-35 Package



DO-7 Package